

**ESD9B5VLD**

**1-Line, Bi-directional, Low-Capacitance,  
Transient Voltage Suppressor**

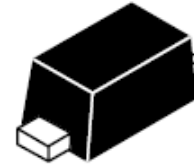
<http://www.sh-willsemi.com>

**Descriptions**

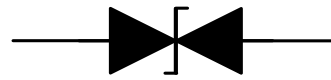
The ESD9B5VLD is a Bi-directional transient voltage suppressor (TVS) to protect sensitive electronic components from electrostatic discharge (ESD). It is particularly well-suited for cellular phones, PMP, MID, PDA, digital cameras and other electronic equipment.

The ESD9B5VLD is safely dissipating ESD strikes to meet the ESD immunity testing of IEC61000-4-2 level 4.

The ESD9B5VLD is available in a SOD-923 package with Pb-free and Halogen-free.



**SOD-923**



**Pin configuration**

**Features**

- Reverse stand-off voltage : 5V Max.
- Peak power (tp=8/20μs) : 36W Max.
- Peak current (tp=8/20μs) : 3A Max.
- Transient protection  
IEC61000-4-2 : ±20KV air  
: ±20KV contact
- Low clamping voltage
- Low leakage current
- Small package



**SOD-923**

**L = Device code  
Marking**

**Order information**

Device	Package	Shipping
ESD9B5VLD-2/TR	SOD-923	10000/Tape&Reel

**Applications**

- Cell phone
- PMP
- MID
- PDA
- Digital camera
- Other electronics equipment

**Absolute maximum ratings**

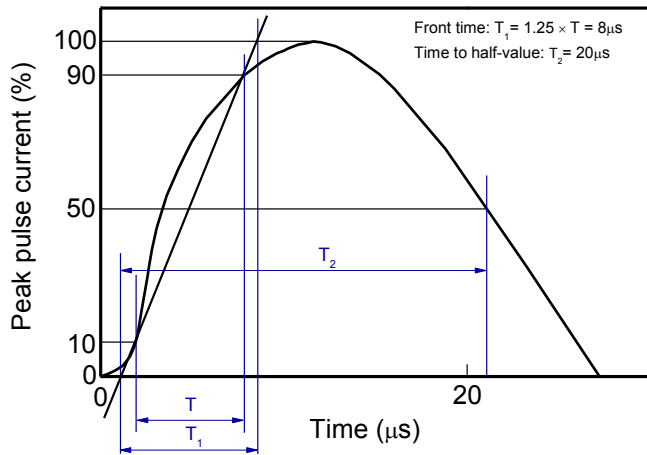
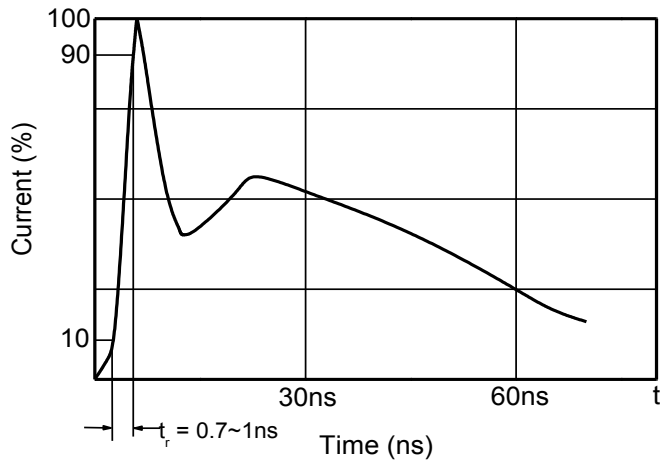
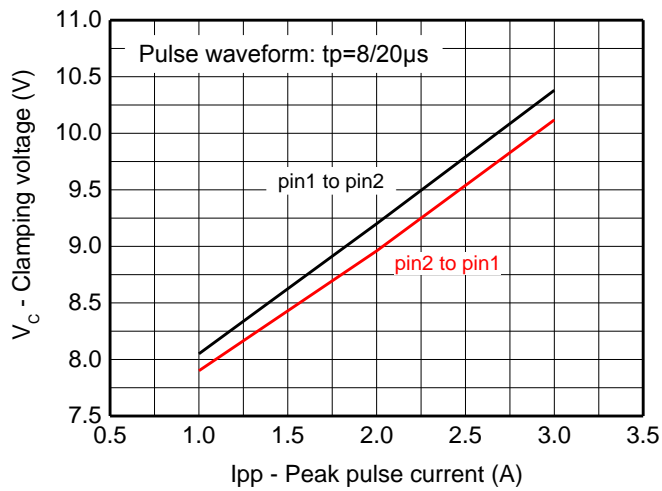
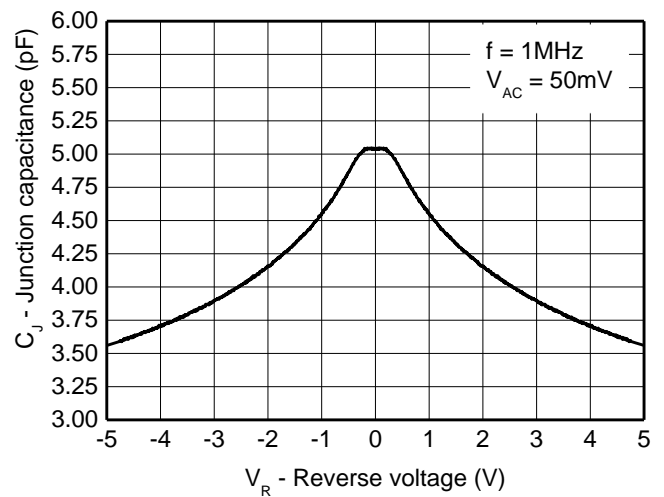
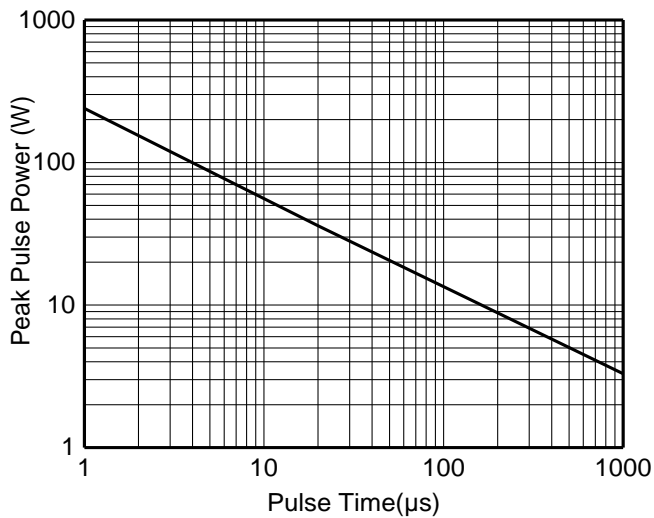
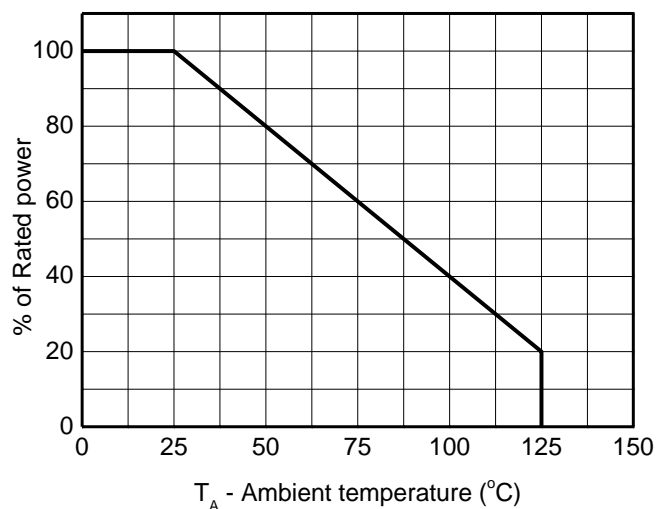
Parameter	Symbol	Rating	Unit
Peak pulse power (tp=8/20μs)	Ppk	36	W
Peak pulse current (tp=8/20μs)	Ipp	3	A
ESD voltage IEC61000-4-2 air	V <sub>ESD</sub>	±20	KV
ESD voltage IEC61000-4-2 contact		±20	
Junction temperature	T <sub>J</sub>	125	°C
Operating temperature	T <sub>OP</sub>	-40~85	°C
Lead temperature	T <sub>L</sub>	260	°C
Storage temperature	T <sub>STG</sub>	-55~150	°C

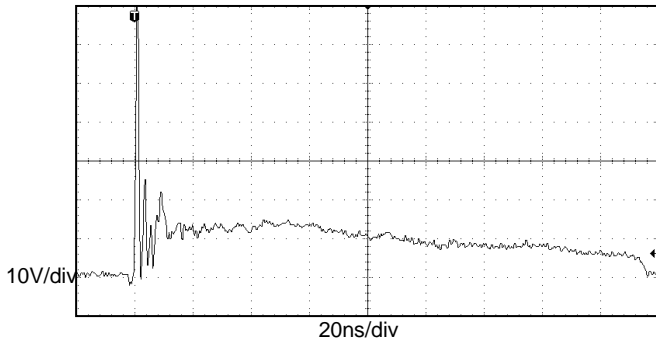
**Electronics characteristics (Ta=25°C, unless otherwise noted)**

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse stand-off voltage	V <sub>RWM</sub>				5.0	V
Reveres leakage current	I <sub>R</sub>	V <sub>RWM</sub> =5V			1.0	μA
Breakdown voltage	V <sub>BR</sub>	I <sub>T</sub> =1mA	6.5		8.2	V
Clamping voltage <sup>1)</sup>	V <sub>CL</sub>	I <sub>PP</sub> = 16A, t <sub>p</sub> = 100ns		13		V
Clamping voltage <sup>2)</sup>	V <sub>CL</sub>	V <sub>ESD</sub> = 8kV		13		V
Clamping voltage <sup>3)</sup>	V <sub>C</sub>	I <sub>pp</sub> =1A tp=8/20μs			8.5	V
		I <sub>pp</sub> =3A tp=8/20μs			12	V
Dynamic resistance <sup>1)</sup>	R <sub>DYN</sub>			0.4		Ω
Junction capacitance	C <sub>J</sub>	V <sub>R</sub> = 0V, f = 1MHz		5	12	pF

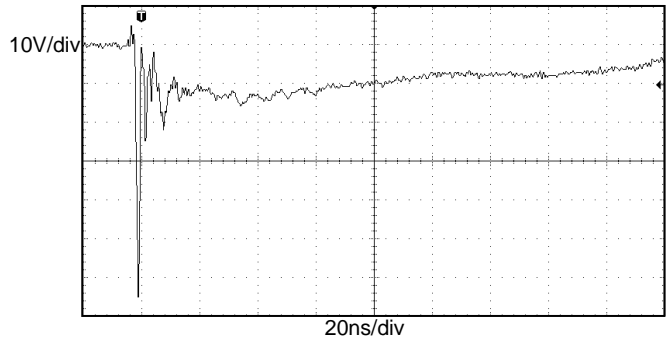
Notes:

- 1) TLP parameter: Z<sub>0</sub> = 50Ω, t<sub>p</sub> = 100ns, t<sub>r</sub> = 2ns, averaging window from 60ns to 80ns. R<sub>DYN</sub> is calculated from 4A to 16A.
- 2) Contact discharge mode, according to IEC61000-4-2.
- 3) Non-repetitive current pulse, according to IEC61000-4-5.

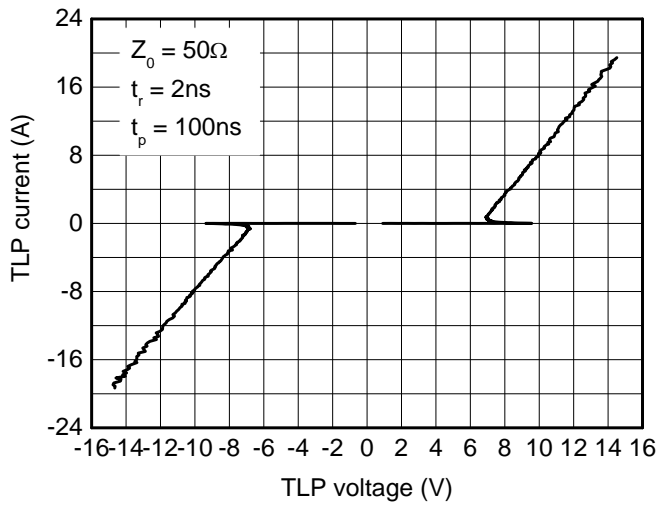
**Typical characteristics ( $T_A=25^\circ\text{C}$ , unless otherwise noted)**

**8/20 $\mu\text{s}$  waveform per IEC61000-4-5**

**Contact discharge current waveform per IEC61000-4-2**

**Clamping voltage vs. Peak pulse current**

**Capacitance vs. Reverse voltage**

**Non-repetitive peak pulse power vs. Pulse time**

**Power derating vs. Ambient temperature**

**Typical characteristics ( $T_A=25^\circ\text{C}$ , unless otherwise noted)**


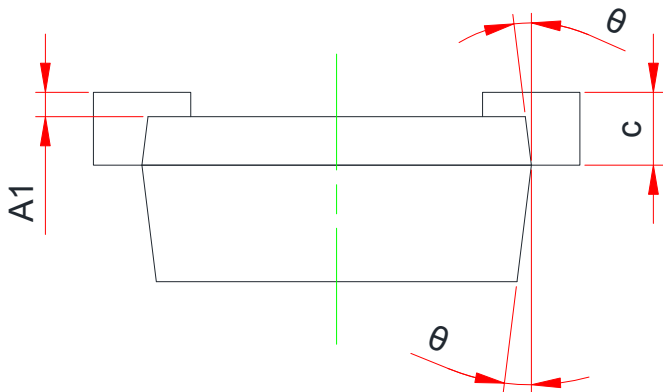
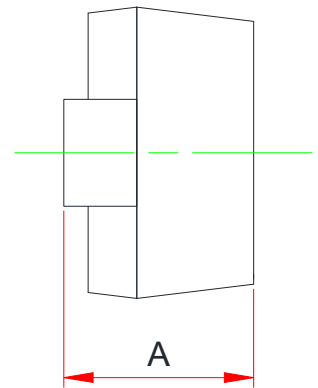
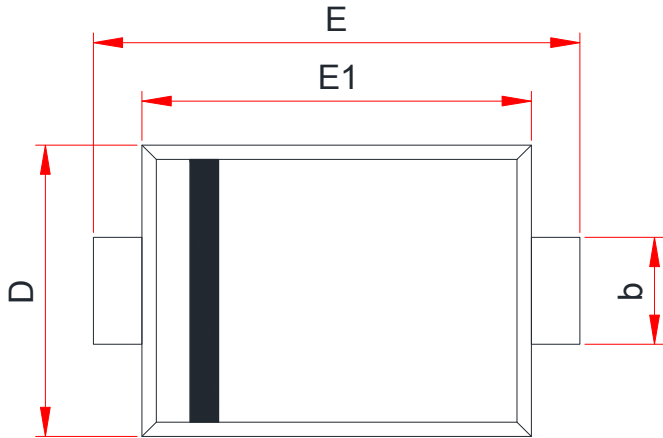
**ESD clamping**  
 (+8kV contact discharge per IEC61000-4-2)



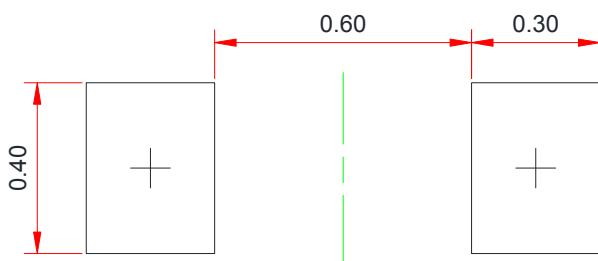
**ESD clamping**  
 (-8kV contact discharge per IEC61000-4-2)



**TLP Measurement**

**Package outline dimensions**
**SOD-923**


Symbol	Dimensions in millimeter		
	Min.	Typ.	Max.
A	0.35	-	0.45
A1	0.00	-	0.05
b	0.15	-	0.27
c	-	-	0.18
D	0.55	0.60	0.65
E	0.90	1.00	1.10
E1	0.75	0.80	0.85
$\theta$	7° Ref.		

**Recommend PCB Layout (Unit: mm)**

**Notes:**

This recommended land pattern is for reference purposes only. Please consult your manufacturing group to ensure your PCB design guidelines are met.